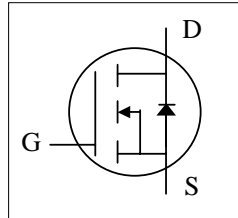




- ▼ Simple Drive Requirement
- ▼ Low On-resistance
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free

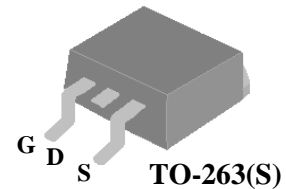


BV_{DSS}	40V
$R_{DS(ON)}$	4.2m Ω
I_D	150A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-263 package is widely preferred for commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current (Chip)	150	A
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^3$	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^3$	80	A
I_{DM}	Pulsed Drain Current ¹	320	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	156	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	3.13	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	0.8	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) ⁴	40	$^\circ C/W$



Electrical Characteristics @T_J=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =40A	-	-	4.2	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	4	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =60A	-	90	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =32V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =40A	-	58	93	nC
Q _{gs}	Gate-Source Charge	V _{DS} =32V	-	12	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	26	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =20V	-	14	-	ns
t _r	Rise Time	I _D =40A	-	83	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =1Ω	-	25	-	ns
t _f	Fall Time	V _{GS} =10V	-	10	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	2600	4160	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	600	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	260	-	pF
R _g	Gate Resistance	f=1.0MHz	-	1.4	2.8	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =40A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _S =10A, V _{GS} =0V,	-	45	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	-	55	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Package limitation current is 80A.
- 4.Surface mounted on 1 in² copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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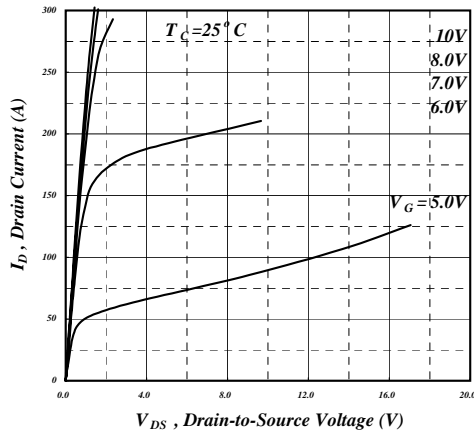


Fig 1. Typical Output Characteristics

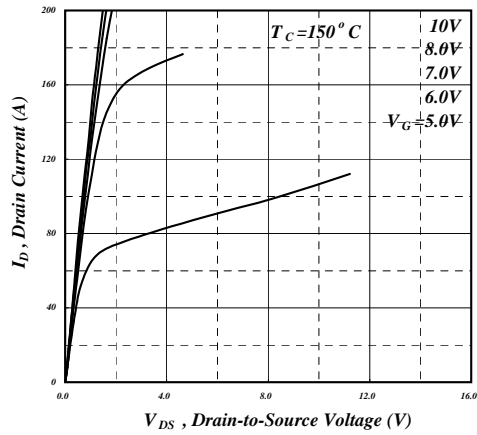


Fig 2. Typical Output Characteristics

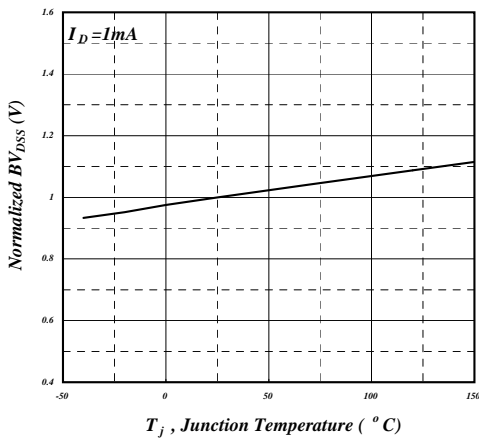


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

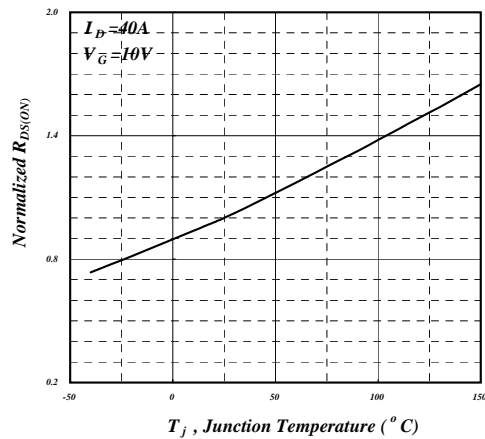


Fig 4. Normalized On-Resistance v.s. Junction Temperature

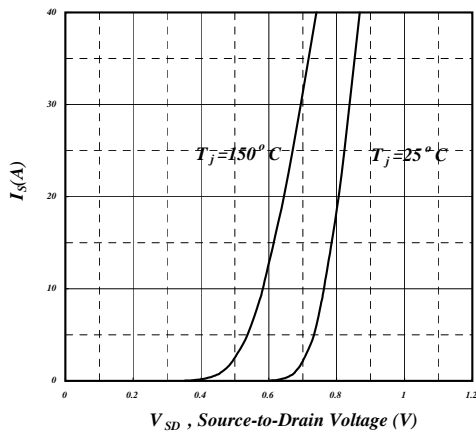


Fig 5. Forward Characteristic of Reverse Diode

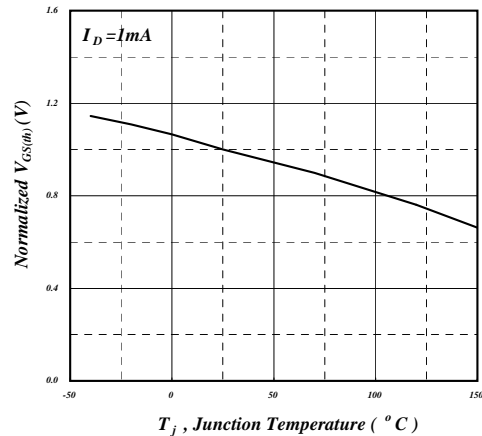


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

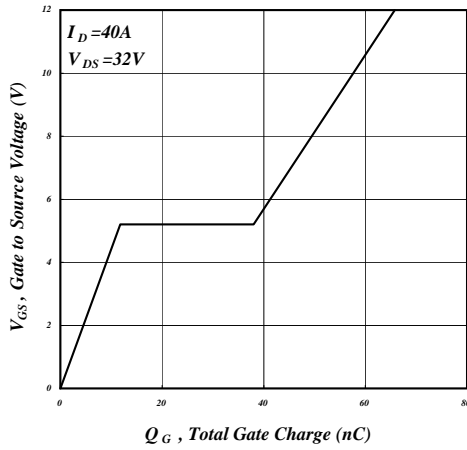


Fig 7. Gate Charge Characteristics

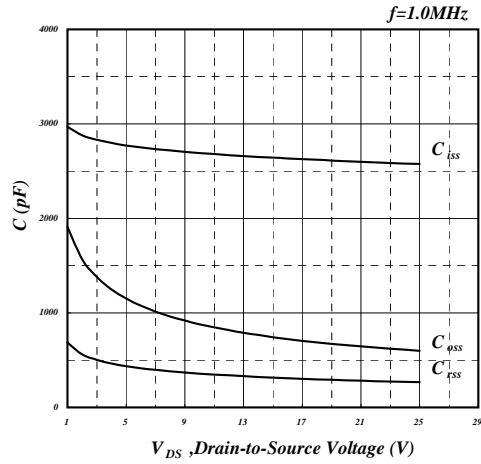


Fig 8. Typical Capacitance Characteristics

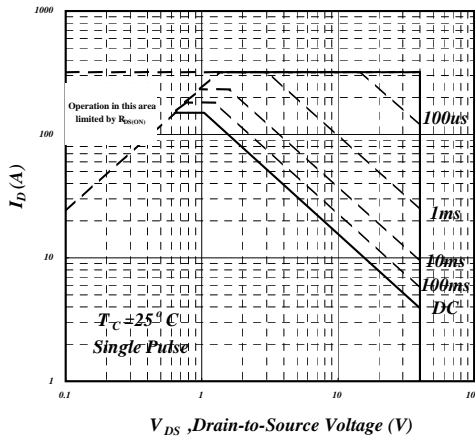


Fig 9. Maximum Safe Operating Area

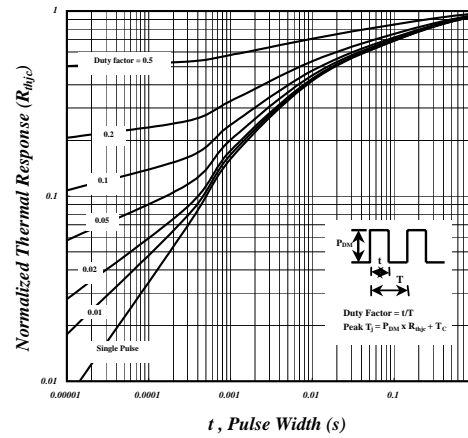


Fig 10. Effective Transient Thermal Impedance

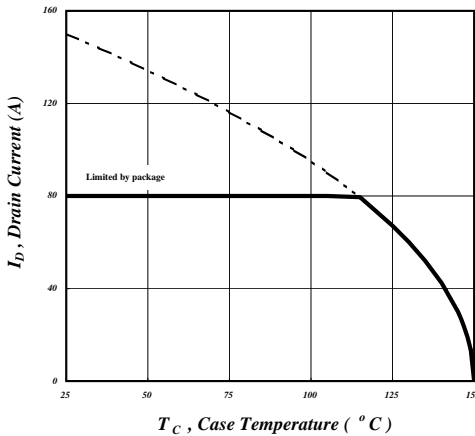


Fig 11. Maximum Continuous Drain Current v.s. Case Temperature

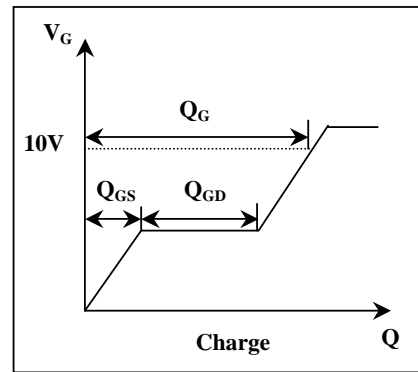


Fig 12. Gate Charge Waveform